

Power MOSFET 130 mAmps, 50 Volts P-Channel

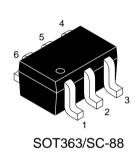
FEATURES:

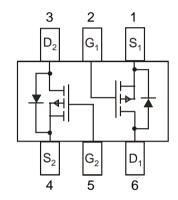
- Energy Efficient
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

APPLICATIONS:

- Low Side Load Switch
- Level Shift Circuits
- DC-DC Converter

Circuit Diagram & Pin Configuration:





DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
BSS84DW1-S03T	PD	3000/Tape&Reel

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	50	Vdc
Gate-to-Source Voltage - Continuous	V_{GS}	± 20	Vdc
Drain Current - Continuous @ T _A = 25°C - Pulsed Drain Current (t _p ≤ 10 μs)	I _D I _{DM}	130 520	mA
Total Power Dissipation @ T _A = 25°C	P _D	380	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Thermal Resistance – Junction–to–Ambient	$R_{\theta JA}$	328	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T _L	260	°C



BSS84DW1-S03T

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS		'		•	•	•
Drain–to–Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc)		V(BR)DSS	50	_	_	Vdc
Zero Gate Voltage Drain Current (VDS = 25 Vdc, VGS = 0 Vdc) (VDS = 50 Vdc, VGS = 0 Vdc) (VDS = 50 Vdc, VGS = 0 Vdc, TJ = 125°C)		IDSS	- - -	- - -	0.1 15 60	μAdc
Gate-Body Leakage Current (VGS = ± 20 Vdc, VDS = 0 Vdc)			_	-	±100	nAdc
ON CHARACTERISTICS (Note 1.)						
Gate–Source Threaded Voltage (V _{DS} = V _{GS} , I _D = 250 μ Adc)		V _{GS(th)}	0.8	_	2.0	Vdc
Static Drain-to-Source On-Resistance (VGS = 5.0 Vdc, I _D = 100 mAdc)		rDS(on)	-	5.0	10	Ohms
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{DS} = 5.0 Vdc)	C _{iss}	_	42	_	pF
Output Capacitance	(V _{DS} = 5.0 Vdc)	C _{oss}	_	20	-	
Transfer Capacitance	(V _{DG} = 5.0 Vdc)	C _{rss}	-	4	-	
SWITCHING CHARACTERISTICS	(Note 2.)	1	•	•	•	•
Turn-On Delay Time		t _d (on)	_	16.7	_	ns
Rise Time	(V _{DS} = -15 V, V _{GS} =-10 V	t _r	-	8.6	-	
Turn-Off Delay Time	$R_L = 50 \Omega, R_G = 25 \Omega$)	t _d (off)	_	17.9	-	
Fall Time		tf	_	5.3	-	1
Gate Charge		Q _T	_	6000	_	рC

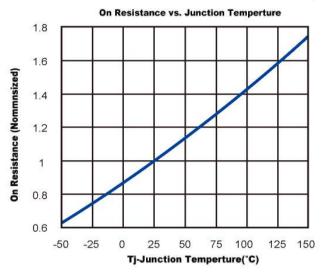
^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

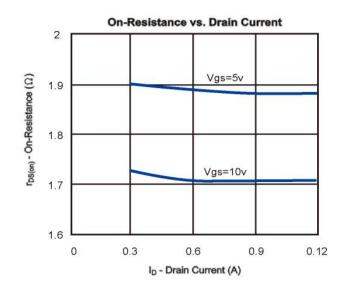
^{2.} Switching characteristics are independent of operating junction temperature.

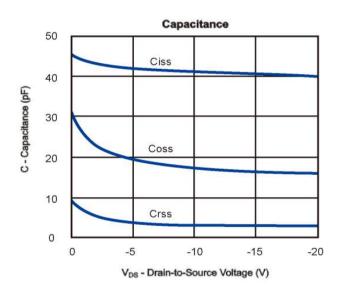


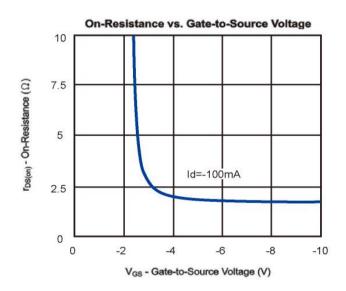
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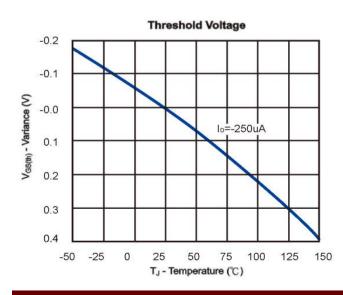
Typical Characteristics (TA =25°C Noted)

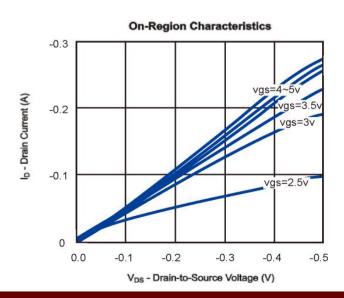








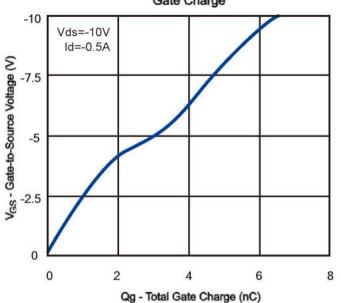


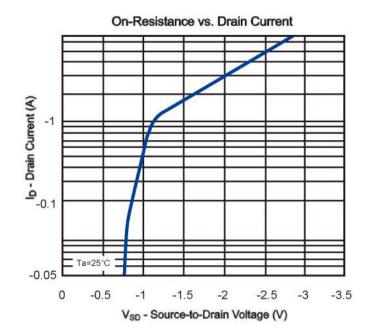








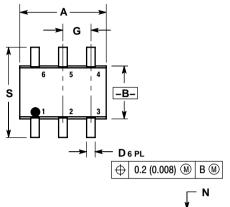


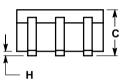


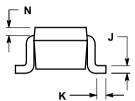




SC-88 (SOT-363)



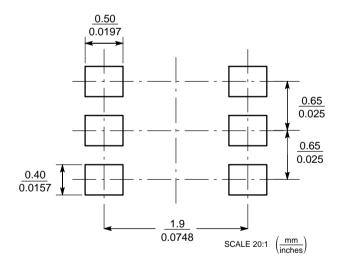




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026 BSC		0.65 BSC		
Н		0.004	0.10		
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	

SOLDERING FOOTPRINT*







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